APM4030NU

N-Channel Enhancement Mode MOSFET

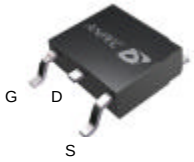
Features

- 40V/35A,
  $R_{DS(ON)}$=17mΩ (typ.) @ V_{GS}=10V
  $R_{DS(ON)}$=26mΩ (typ.) @ V_{GS}=4.5V
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

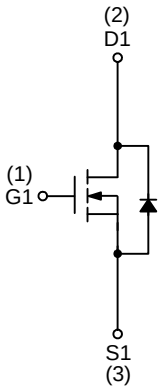
Applications

- Inverter Application in LCM and LCD TV

Pin Description



Top View of TO-252



N-Channel MOSFET

Ordering and Marking Information

APM4030N □□-□□ □

- Assembly Material
- Handling Code
- Temp. Range
- Package Code

Package Code
U : TO-252
Operating Junction Temp. Range
C : -55 to 150° C
Handling Code
TR : Tape & Reel
Assembly Material
L : Lead Free Device
G : Halogen and Lead Free Device

APM4030N U :

XXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020C for MSL classification at lead-free peak reflow temperature. ANPEC defines “Green” to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T_A = 25°C Unless Otherwise Noted)				
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	T_C=25°C	10	A
Mounted on Large Heat Sink				
I_{DP}	300µs Pulse Drain Current Tested	T_C=25°C	80	A
		T_C=100°C	52	
I_D	Continuous Drain Current	T_C=25°C	35	A
		T_C=100°C	23	
P_D	Maximum Power Dissipation	T_C=25°C	50	W
		T_C=100°C	20	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		2.5	°C/W
Mounted on PCB of 1in^2 Pad Area				
I_{DP}	300µs Pulse Drain Current Tested	T_A=25°C	32	A
		T_A=100°C	20	
I_D	Continuous Drain Current	T_A=25°C	8	A
		T_A=100°C	5	
P_D	Maximum Power Dissipation	T_A=25°C	2.5	W
		T_A=100°C	1	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		50	°C/W
Mounted on PCB of Minimum Footprint				
I_{DP}	300µs Pulse Drain Current Tested	T_A=25°C	24	A
		T_A=100°C	16	
I_D	Continuous Drain Current	T_A=25°C	6	A
		T_A=100°C	4	
P_D	Maximum Power Dissipation	T_A=25°C	1.6	W
		T_A=100°C	0.6	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		75	°C/W

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	40			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=32V, V_{GS}=0V			1	μA
		T_J=85°C			30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1.3	2	2.5	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$R_{DS(ON)}$ [a]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=12A		17	25	mΩ
		V_{GS}=4.5V, I_{DS}=6A		26	40	
Diode Characteristics						
V_{SD} [a]	Diode Forward Voltage	I_{SD}=2A, V_{GS}=0V		0.8	1.1	V
t_{rr}	Reverse Recovery Time	I_{SD}=10A, dI_{SD}/dt =100A/μs		20		ns
Q_{rr}	Reverse Recovery Charge			14		nC
Dynamic Characteristics [b]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz		1.6		Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=20V, Frequency=1.0MHz		950		pF
C_{oss}	Output Capacitance			115		
C_{rss}	Reverse Transfer Capacitance			75		
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=20V, R_L=20Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω		15.6	30	ns
T_r	Turn-on Rise Time			19	29	
$t_{d(OFF)}$	Turn-off Delay Time			30	55	
T_f	Turn-off Fall Time			7	14	
Gate Charge Characteristics [b]						
Q_g	Total Gate Charge	V_{DS}=20V, V_{GS}=10V, I_{DS}=12A		18.2	23.5	nC
Q_{gs}	Gate-Source Charge			2.2		
Q_{gd}	Gate-Drain Charge			6		

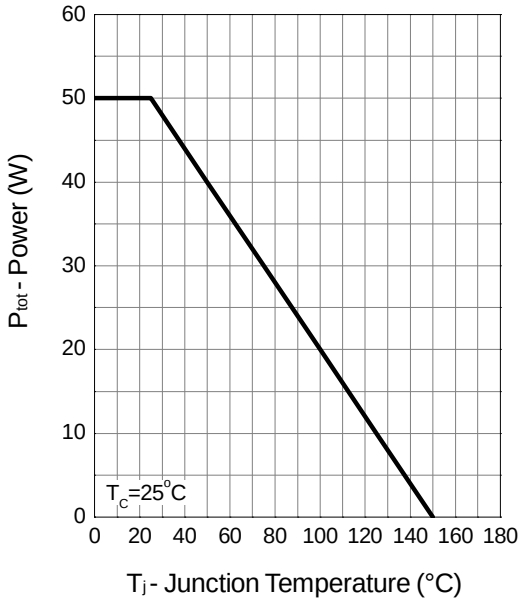
Notes:

a : Pulse test ; pulse width ≤300μs, duty cycle ≤ 2%.

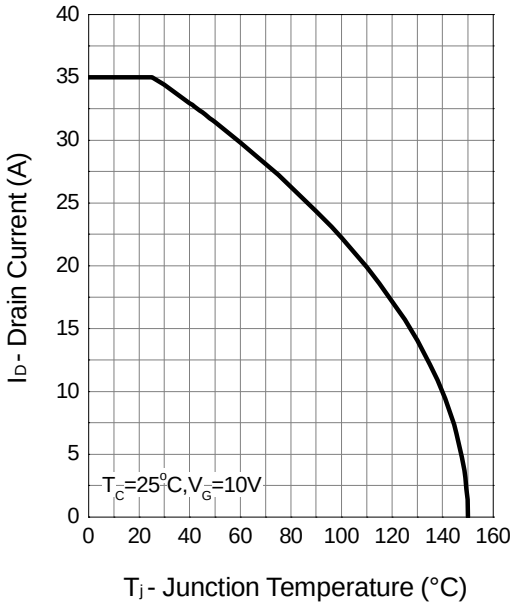
b : Guaranteed by design, not subject to production testing.

Typical Characteristics

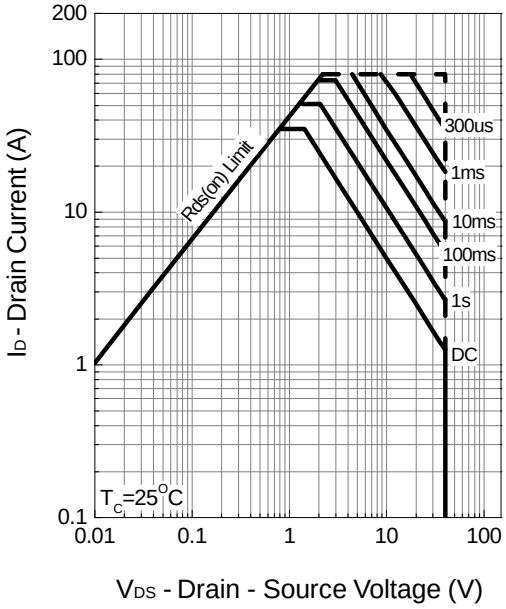
Power Dissipation



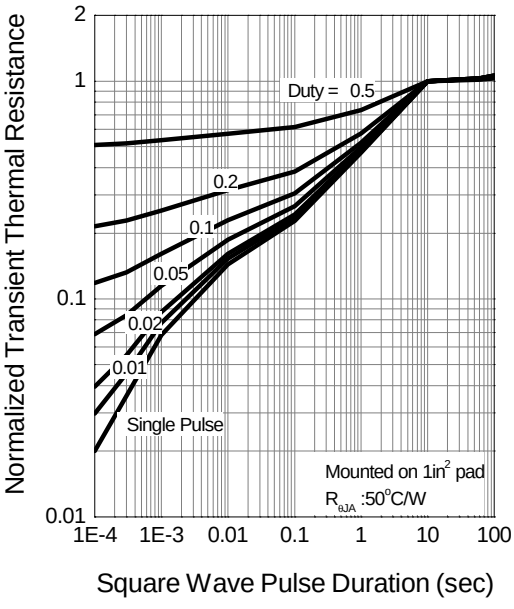
Drain Current



Safe Operation Area

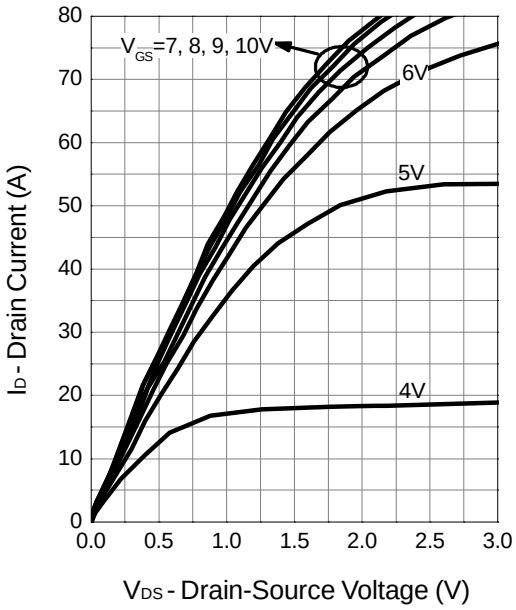


Thermal Transient Impedance

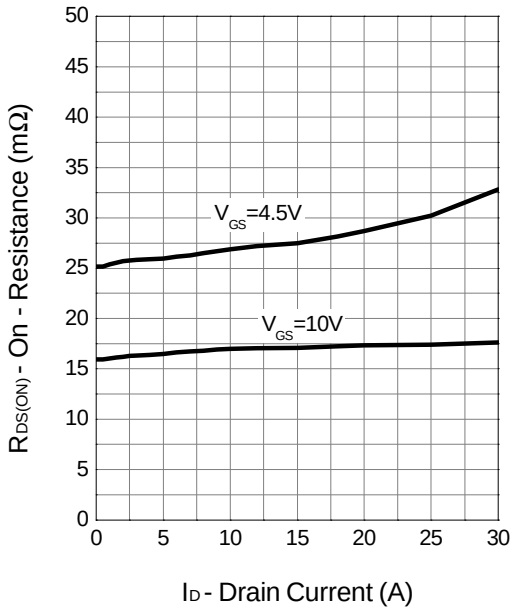


Typical Characteristics (Cont.)

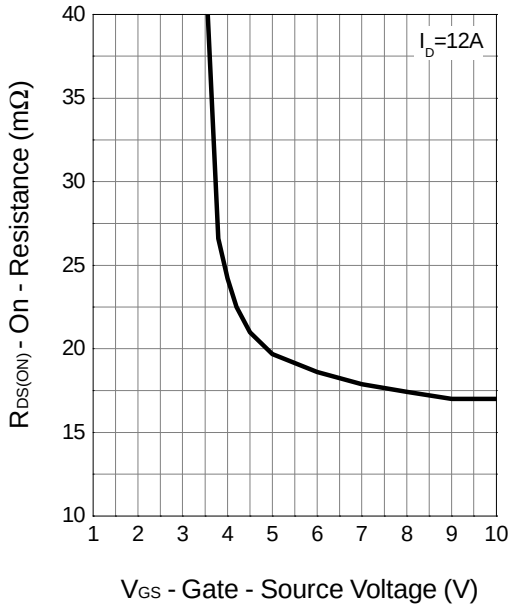
Output Characteristics



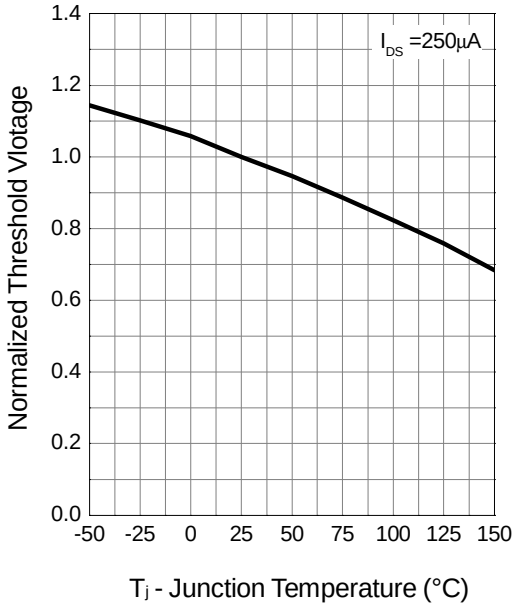
Drain-Source On Resistance



Drain-Source On Resistance

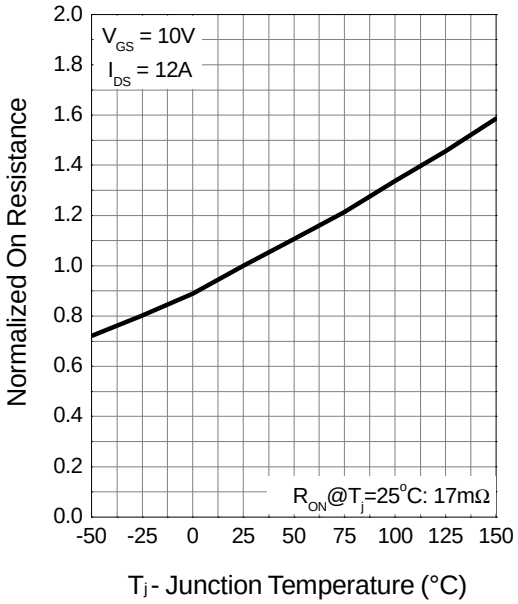


Gate Threshold Voltage

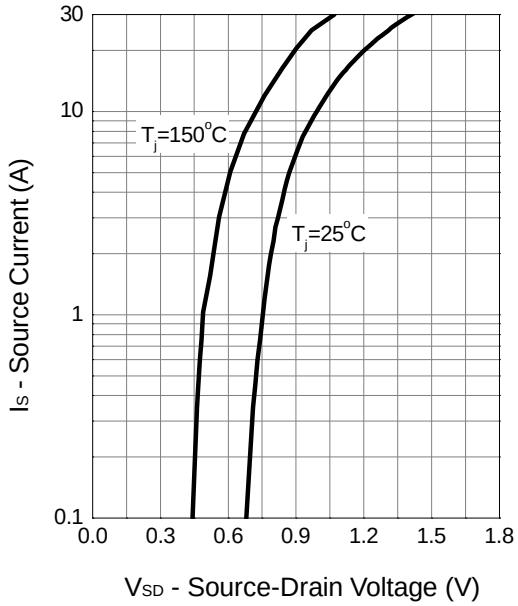


Typical Characteristics (Cont.)

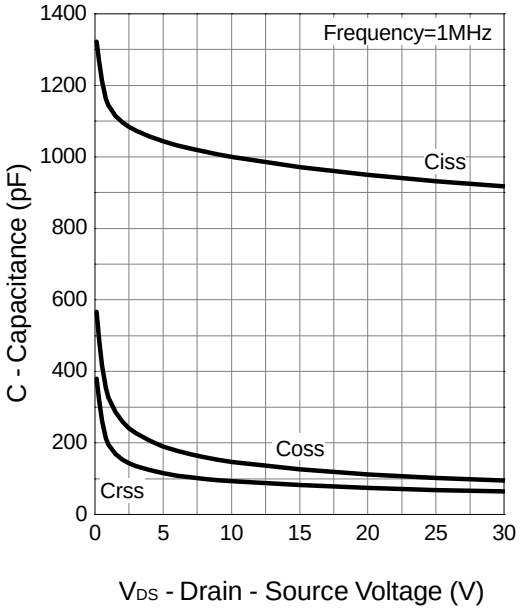
Drain-Source On Resistance



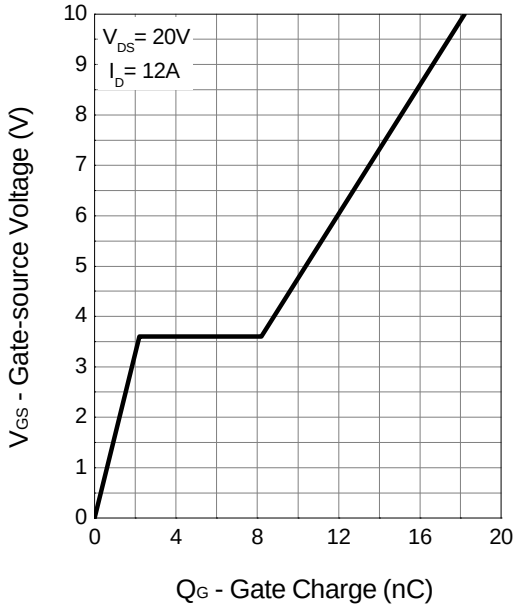
Source-Drain Diode Forward



Capacitance

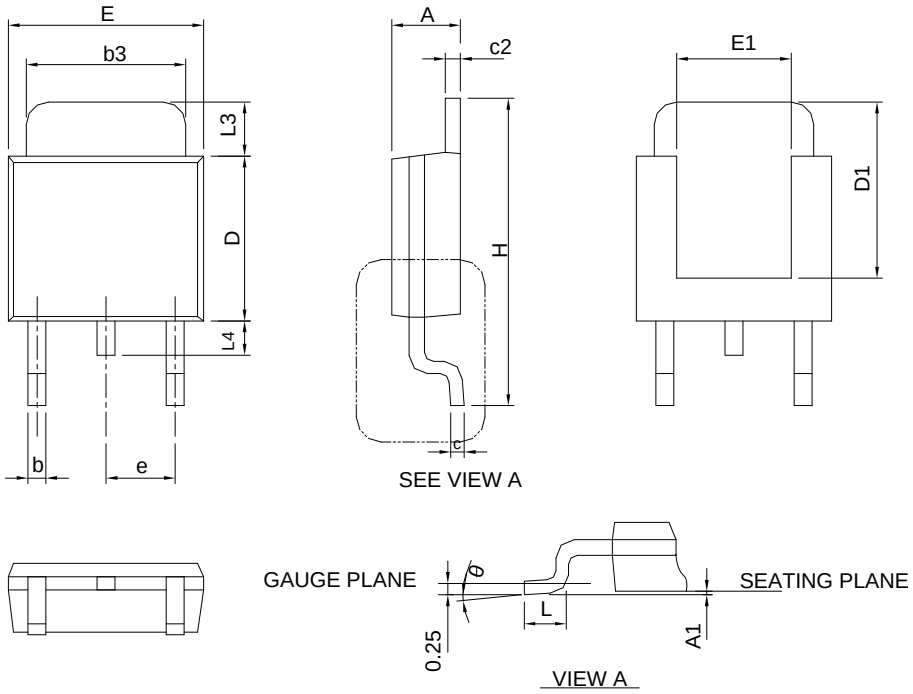


Gate Charge



Package Information

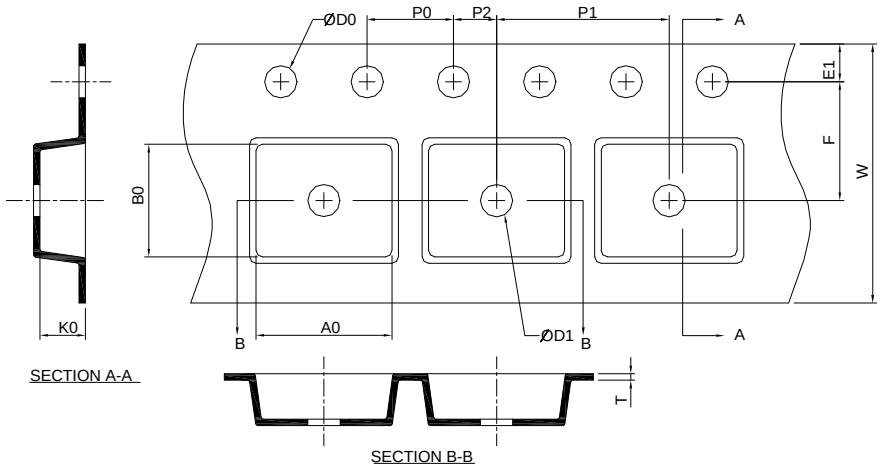
TO-252

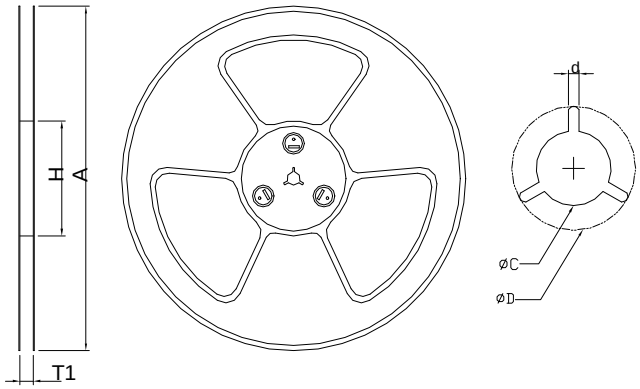


SYMBOL	TO-252			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1		0.13		0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.235
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.235
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4		1.02		0.040
θ	0°	8°	0°	8°

Note : Follow JEDEC TO-252 .

Carrier Tape & Reel Dimensions





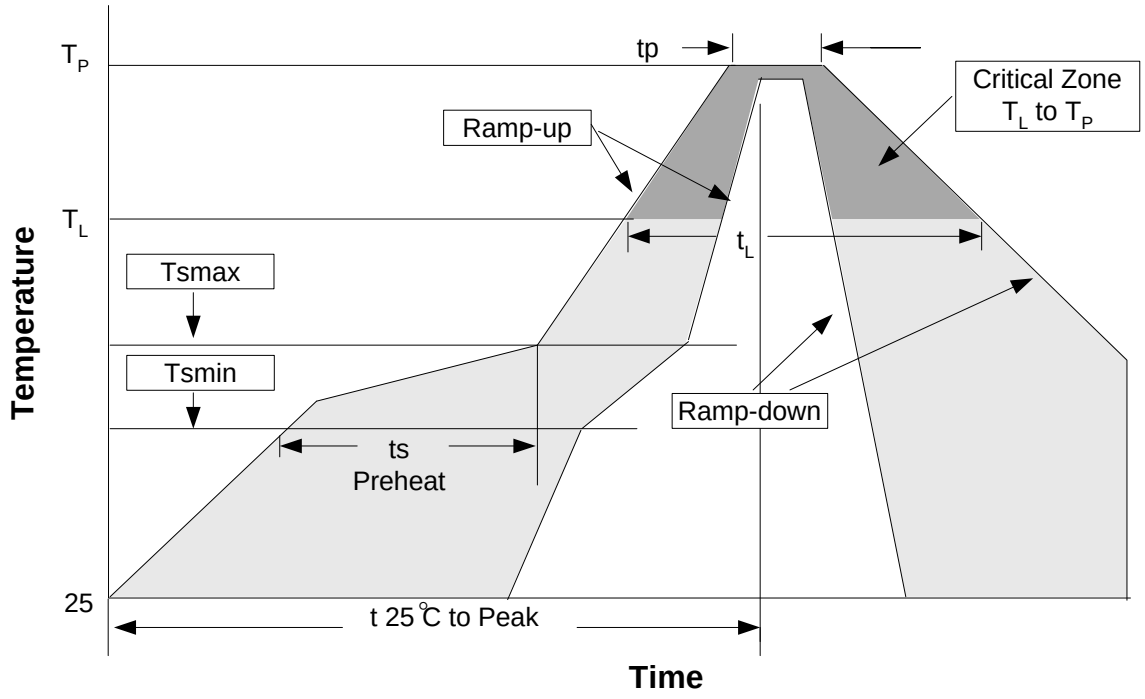
Application	A	H	T1	C	d	D	W	E1	F
TO-252	330.0±2.00	50 MIN.	16.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	16.0±0.30	1.75±0.10	7.50±0.05
	P0	**P1**	**P2**	**D0**	**D1**	**T**	**A0**	**B0**	**K0**
	4.0±0.10	8.0±0.10	2.0±0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.80±0.20	10.40±0.20	2.50±0.20

(mm)

Devices Per Unit

Package Type	Unit	Quantity
TO-252	Tape & Reel	2500

Reflow Condition (IR/Convection or VPR Reflow)



Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 sec
HOLT	MIL-STD-883D-1005.7	1000 Hrs Bias @125°C
PCT	JESD-22-B, A102	168 Hrs, 100%RH, 121°C
TST	MIL-STD-883D-1011.9	-65°C~150°C, 200 Cycles

Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (Tsmin) - Temperature Max (Tsmax) - Time (min to max) (ts)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classification Temperature (Tp)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (tp)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Note: All temperatures refer to topside of the package. Measured on the body surface.

Classification Reflow Profiles (Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm^3 <350	Volume mm^3 350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

Package Thickness	Volume mm^3 <350	Volume mm^3 350-2000	Volume mm^3 >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*
*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.			

Customer Service

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